

# Super323™ SOT323 PNP SILICON POWER (SWITCHING) TRANSISTOR

## ZUMT717

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### FEATURES

- \* **500mW POWER DISSIPATION**
- \* **I<sub>C</sub> CONT 1.5A**
- \* 3A Peak Pulse Current
- \* Excellent H<sub>FE</sub> Characteristics Up To 3A (pulsed)
- \* Extremely Low Saturation Voltage
- \* Extremely Low Equivalent On Resistance; R<sub>CE(sat)</sub>



### APPLICATIONS

- \* Negative boost functions in DC-DC converters
- \* Supply line switching in mobile phones and pagers
- \* Motor drivers in camcorders and mini disk players

DEVICE TYPE	COMPLEMENT	PARTMARKING	R <sub>CE(sat)</sub>
ZUMT717	ZUMT617	T71	150mΩ at 1.25A

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-12	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-12	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Peak Pulse Current**	I <sub>CM</sub>	-3	A
<b>Continuous Collector Current</b>	<b>I<sub>C</sub></b>	<b>-1.25</b>	<b>A</b>
Base Current	I <sub>B</sub>	-200	mA
<b>Power Dissipation at T<sub>amb</sub>=25°C*</b>	<b>P<sub>tot</sub></b>	<b>385 †</b> <b>500 ‡</b>	<b>mW</b>
Operating and Storage Temperature Range	T <sub>J</sub> ; T <sub>stg</sub>	-55 to +150	°C

† Recommended P<sub>tot</sub> calculated using FR4 measuring 10 x 8 x 0.6mm (still air).

‡ Maximum power dissipation is calculated assuming that the device is mounted on FR4 size 25x25x0.6mm and using comparable measurement methods adopted by other suppliers.

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## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-12			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-12			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			-10	nA	$V_{CB} = -10\text{V}$
Emitter Cut-Off Current	$I_{EBO}$			-10	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	$I_{CES}$			-10	nA	$V_{CES} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-25 -55 -110 -160 -185	-40 -100 -175 -215 -240	mV mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.25\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.5\text{A}, I_B = -10\text{mA}^*$ $I_C = -1\text{A}, I_B = -50\text{mA}^*$ $I_C = -1.25\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-990	-1100	mV	$I_C = -1.25\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-850	-1000	mV	$I_C = -1.25\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	300 300 200 125 75 30	490 450 340 250 140 80			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -0.1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -0.5\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -1.25\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -3\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	$f_T$		220		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$		15		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		50		ns	$V_{CC} = -10\text{V}, I_C = -1\text{A}$ $I_{B1} = I_{B2} = -100\text{mA}$
Turn-Off Time	$t_{(off)}$		135		ns	

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## TYPICAL CHARACTERISTICS

